

GSM3385DF

30V P-Channel MOSFETs

Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

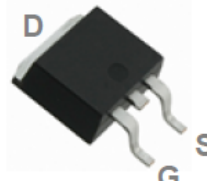
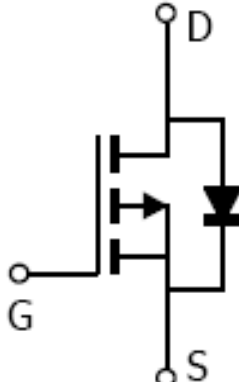
Features

- -30V, -70A, $R_{DS(ON)} < 8.5m\Omega @ V_{GS} = -10V$
- Fast switching
- Suit for -4.5V Gate Drive Applications
- Green Device Available
- TO-252-2L package design

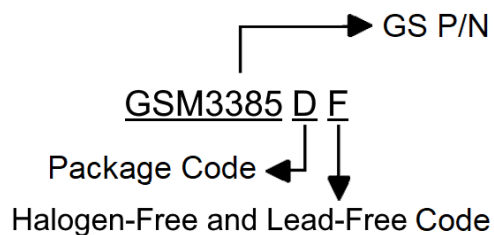
Applications

- MB / VGA / Vcore
- POL Applications
- Load Switch
- LED Application

Packages & Pin Assignments

GSM3385DF (TO-252-2L)		
 Top View		
Description		
Gate		
Drain		
Source		

Ordering Information



Part Number	Package	Quantity Reel
GSM3385DF	TO-252-2L	2500 PCS

Marking Information



Absolute Maximum Ratings

T_C=25°C Unless otherwise noted

Symbol	Parameter		Typical	Unit
V _{DS}	Drain-Source Voltage		-30	V
V _{GS}	Gate-Source Voltage		±25	V
I _D	Continuous Drain Current	T _C =25°C	-70	A
		T _C =100°C	-44	
I _{DM}	Pulsed Drain Current ¹		-180	A
P _D	Power Dissipation	T _C =25°C	62.5	W
		T _C =100°C	25	
T _J	Operating Junction Temperature Range		-55 to +150	°C
T _{STG}	Storage Temperature Range		-55 to +150	°C
R _{θJC}	Thermal Resistance-Junction to Case		2	°C/W

Electrical Characteristics

T_J=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1.2	-1.6	-2.5	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±25V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V			-1	uA
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _S =-1A			-1	V
R _{DS(on)}	Drain-Source On-Resistance ³	V _{GS} =-10V, I _D =-20A		7.2	8.5	mΩ
		V _{GS} =-4.5V, I _D =-10 A		11.5	14	
Gate charge characteristics						
Q _g	Total Gate Charge ^{3,4}	V _{DD} =-15V, V _{GS} =10V, I _D =-15A		68		nC
Q _{gs}	Gate-Source Charge ^{3,4}			10		
Q _{gd}	Gate-Drain Charge ^{3,4}			12		
Dynamic characteristics						
C _{iSS}	Input Capacitance	V _{DS} =-15V,V _{GS} =0V, f=1.0MHz		4319		pF
C _{oSS}	Output Capacitance			439		
C _{rSS}	Reverse Transfer Capacitance			299		
t _{d(on)}	Turn-On Time	V _{DD} =-15V, V _{GS} =-10V, R _g =3.3Ω, I _D =-15A		12		ns
t _r	Rise Time			11		
t _{d(off)}	Turn-Off Time			105		
t _f	Fall Time			21		

Typical Performance Characteristics

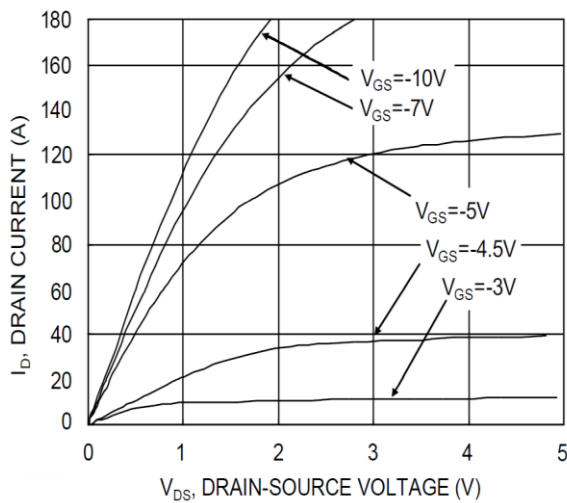


Figure 1. Output Characteristics

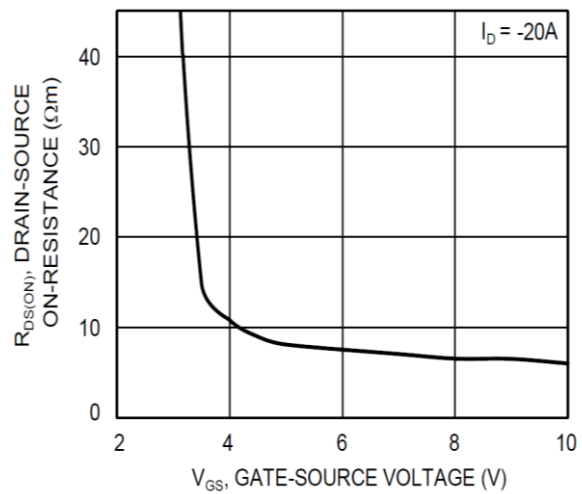


Figure 2. On-Resistance Variation with V_{GS}

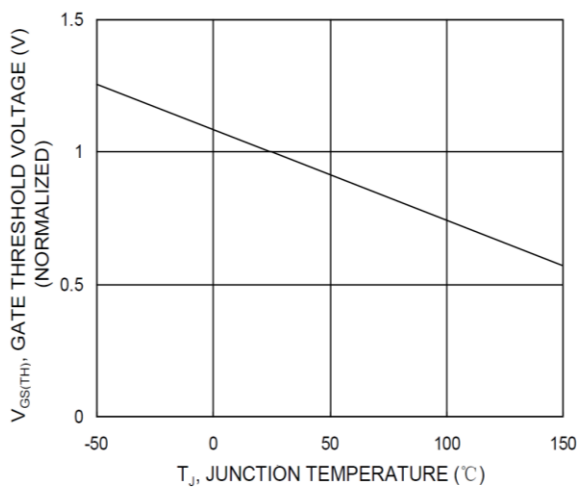


Figure 3. Normalized $V_{GS(th)}$ vs. T_J

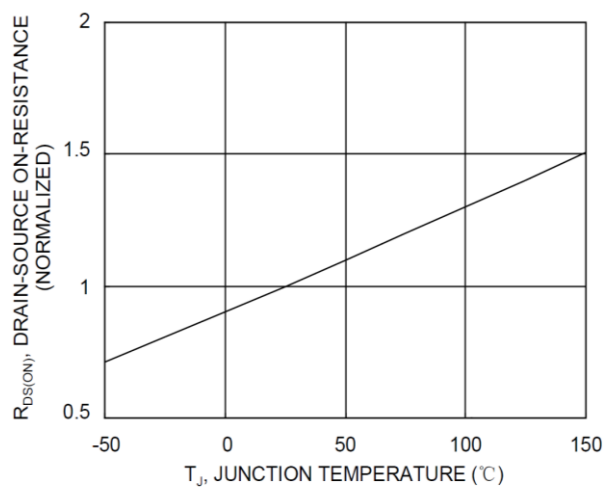


Figure 4. Normalized $R_{DS(on)}$ vs. T_J

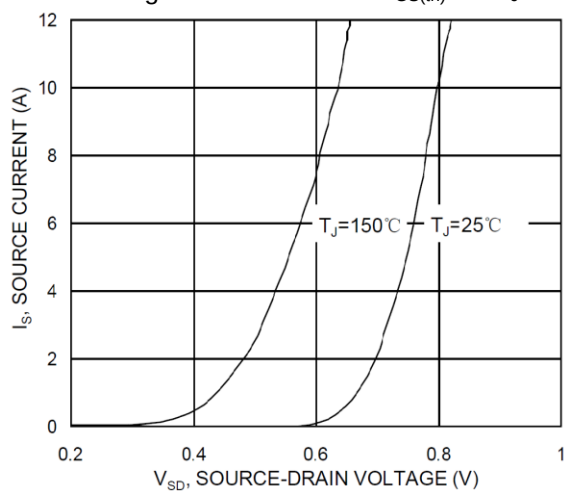


Figure 5. Diode Forward Voltage vs. Current

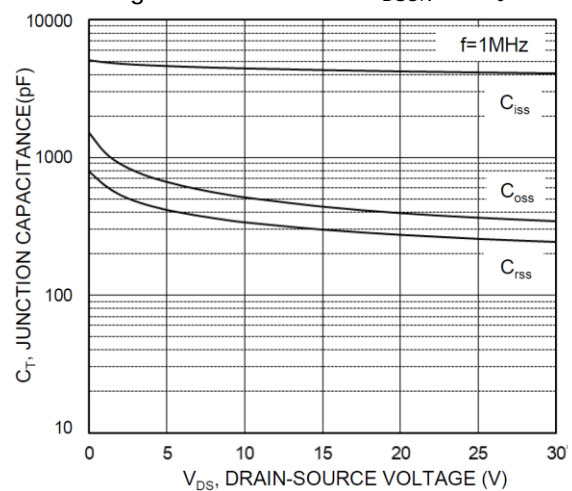


Figure 6. Capacitance

Typical Performance Characteristics (Continue)

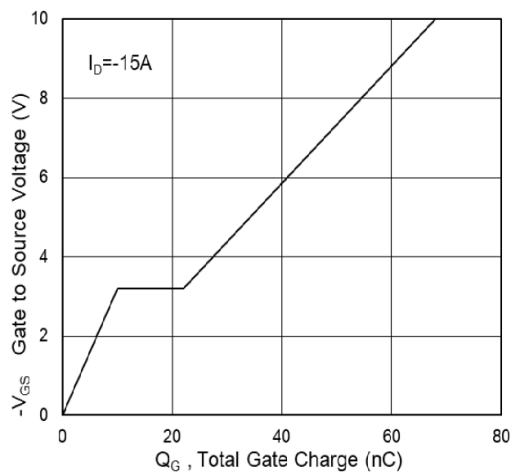


Figure 7. Gate Charge Waveform

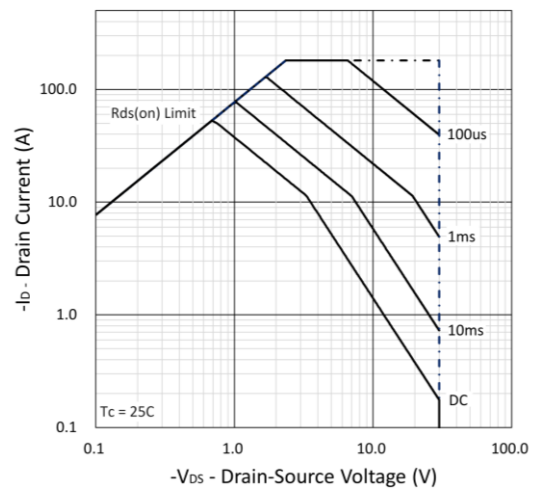


Figure 8. Maximum Safe Operating Area

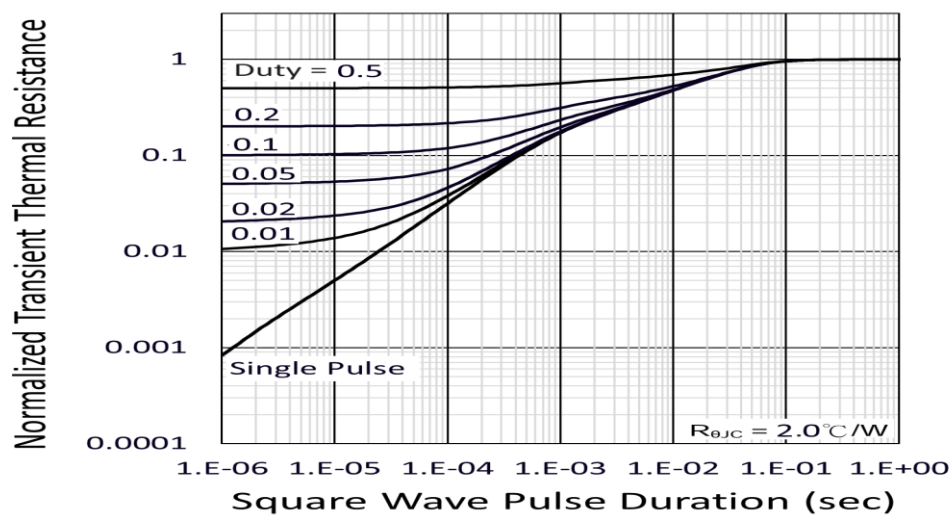
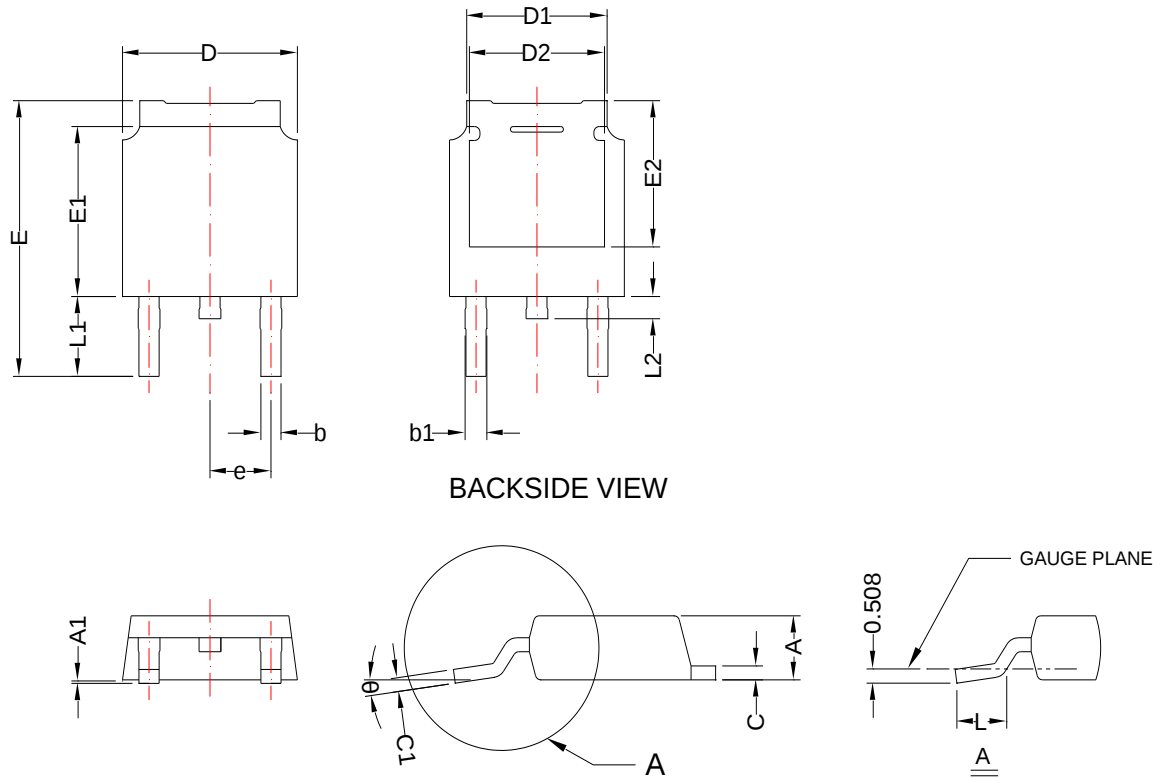


Figure 9. Normalized Transient Thermal Resistance

Package Dimension

TO-252(AA)



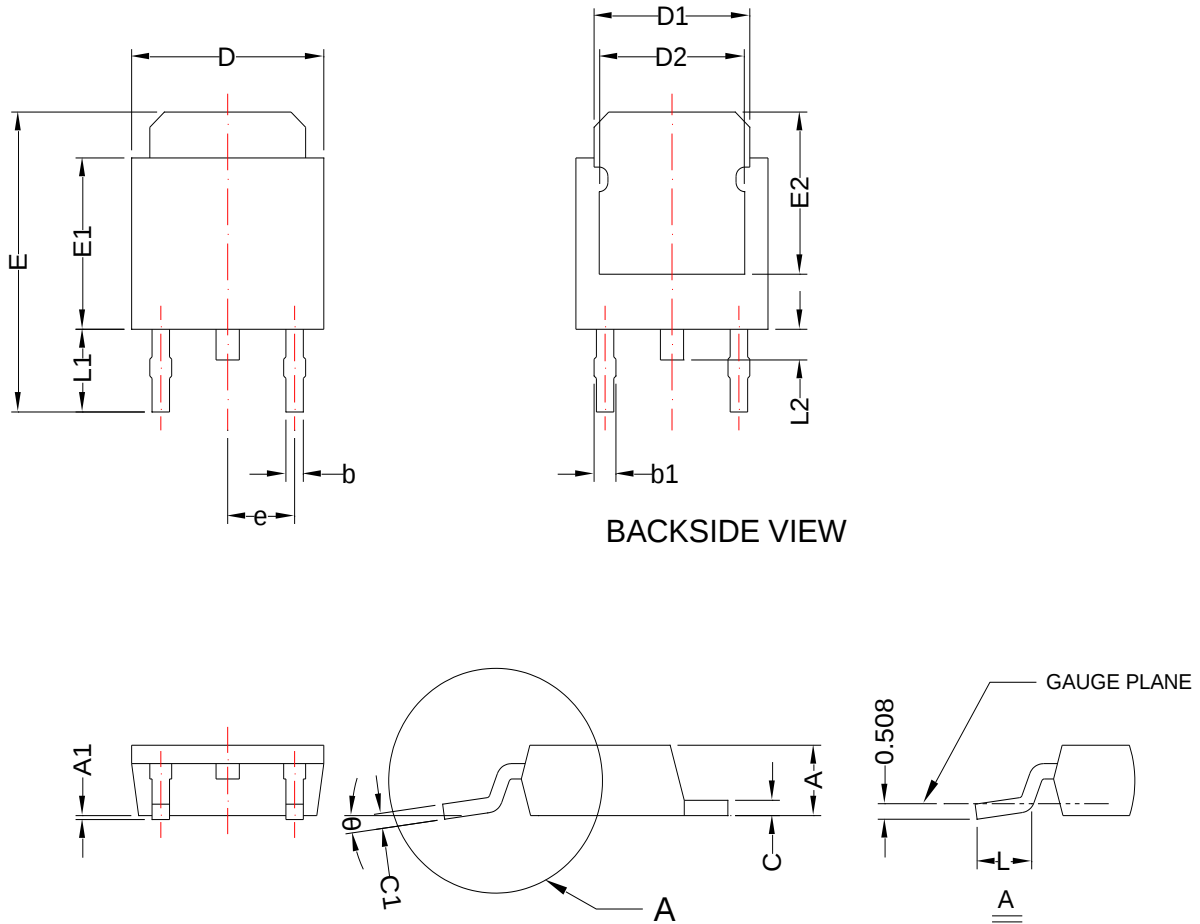
THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMS OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.

DIMENSION D DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.15mm PER DNE. DIMENSION E1 DOES NOT INCLUDE MOLD FLASH, PROTRUSION. OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL EXCEED 0.15mm INCHES PER DNE.

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.18	2.40	0.086	0.094
A1	0.00	0.15	0.000	0.006
b	0.64	0.90	0.025	0.035
b1	0.76	1.14	0.030	0.045
c	0.40	0.89	0.016	0.035
c1	0.40	0.61	0.016	0.024
D	6.35	6.73	0.250	0.265
D1	4.95	5.46	0.195	0.215
D2	4.32	---	0.170	---

E	9.40	10.41	0.370	0.410
E1	5.97	6.22	0.235	0.245
E2	4.95	---	0.195	---
e	2.286 BSC		0.090 BSC	
L	1.40	1.77	0.055	0.070
L1	2.67	3.07	0.105	0.121
L2	---	1.20	---	0.047
θ	0°	8°	0°	8°

TO-252(AB)



DIMENSION D DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.15mm PER DNE. DIMENSION E1 DOES NOT INCLUDE MOLD FLASH, PROTRUSION. OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL EXCEED 0.15mm INCHES PER DNE.

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.18	2.40	0.086	0.094
A1	0.00	0.15	0.000	0.006
b	0.50	0.90	0.020	0.035
b1	0.60	1.14	0.024	0.045
c	0.45	0.89	0.018	0.035
c1	0.40	0.61	0.016	0.024
D	6.35	6.80	0.250	0.268
D1	4.95	5.50	0.195	0.217
D2	3.81	---	0.150	---
E	9.40	10.41	0.370	0.410

E1	5.33	5.80	0.210	0.228
E2	4.57	---	0.180	---
e	2.286 BSC		0.090 BSC	
L	1.40	1.78	0.055	0.070
L1	2.40	3.00	0.094	0.118
L2	---	1.20	---	0.047
θ	0°	8°	0°	8°

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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihsu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587